Mr Chairman:

As we celebrate our fifth anniversary, and as an established member of the academic and scientific communities, we seek now to make our campus more international, and more Chinese. It is fitting therefore, that we should honour today some-one who is not only a world leader in scientific research, but also generally recognised as one of the Chinese scientists most responsible for the promotion of academic exchange and collaboration between China and other countries, particularly the United States.

Professor XIE XIDE, erstwhile President of Fudan University in Shanghai, and currently Professor of Physics there, first graduatd with a BS in Physics from Xiamen University, but subsequently took her MA in Physics from Smith College, and her PhD in Physics from the Massachusetts Institute of Technology, specialising in solid state theory.

She returned to China via the United Kingdom to take up a lectureship in the Department of Physics at Fudan University, where she has spent her entire career as a teacher, researcher and administrator. After a period as Adjunct Director of the Shanghai Institute of Technical Physics of the Chinese Academy of Sciences, she was nominated Vice-President of Fudan University, a post she held from 1978 to 1983. From 1978 to 1983, she was also Director of the Institute of Modern Physics at Fudan University. And from 1983 to 1988, she held the Presidency of the University. Fudan is one of China's leading universities, and its reputation is due in no small part to Professor Xie's work in the evolution of science in China, through her truly pioneering contributions in the very early days of the development of semiconductor physics.

She has authored four books, and over 60 research papers in the fields of energy bands of solids, and the electronic states of surfaces and interfaces. Her co-authored book "Semiconductor Physics" was one of the first published in China on the subject. She still leads a research group in surface science in China, and is in collaboration with colleagues worldwide, including those at our own University, in research on semiconductor surfaces and interfaces. She and her colleagues have made key contributions in this area, providing insights into questions of geometrical structures and vibrational spectra in heterojunctions and superlattices.

During her career, she spent two years at Peking University training groups in semiconductor physics. Many of her students are now professors in leading universities or research centres.

She is an elected member of the Chinese Academy of Sciences, and a Fellow of the Third World Academy of Sciences and the American Physical Society and a Foreign Honorary Member of the American Academy of Arts and Sciences.

Highly regarded by the international academic community, Professor Xie has already received ten honorary doctorates from universities in the United States, Canada, the United Kingdom and Japan. Fully aware of the importance of international exposure in the dissemination of research, she played a key role in the establishment of educational programmes and a research infrastructure, offering opportunities to young researchers in China to participate in the activities of the international community, through study visits and conference attendance.

Mr Chairman, it is my privilege to recommend, on behalf of the University, one of China's most distinguished scientists, Professor Xie Xide, Academician, Professor of Physics and Director of the Centre for American Studies at Fudan University, for the degree of Doctor of Science honoris causa.